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a cassette stage for mounting a cassette having wafers stacked thereon;  
a transfer path adjacent to the cassette stage for providing space for transportation of wafers, the transfer path being at atmospheric pressure [having a width slightly larger than a diameter of the wafers];  
a plurality of processing chambers aligned with the transfer path; and  
a transfer mechanism installed in the transfer path for loading and unloading the wafers stacked on the cassette stage to the plurality of processing chambers.

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3. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 1, wherein each processing chamber has a gate formed on a side [facing] away from the transfer path, the gate being selectively opened and closed to allow passage of the wafers.

*gate door valve*

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20. (Amended) A multi-chamber system of an etching facility for manufacturing semiconductor devices comprising:

a cassette stage for mounting a cassette having wafers stacked thereon;  
a transfer path adjacent to the cassette stage for providing space for transportation of wafers, the transfer path being at atmospheric pressure and having a width slightly larger than a diameter of the wafers;  
a plurality of processing chambers aligned in a plurality of layers [multi-layers] parallel to and beside the transfer path; and

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B [ a transfer mechanism capable of vertical/horizontal reciprocal movement installed in the transfer path for loading and unloading the wafers stacked on the cassette stage to the plurality of processing chambers.

22. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 20, wherein the plurality of layers [multi-layers] of the processing chambers include [number] 2 to 5 layers.

24. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 23, wherein the load lock chamber comprises:  
a transfer arm for receiving wafers from the transfer mechanism and transferring the wafers to the processing [chamber] chambers;  
an inner transfer device for moving the transfer arm; and  
gates formed on a side of the transfer path and [a side] sides of the processing chambers [chamber], respectively, the gates being selectively opened and closed to allow passage of the wafers.

26. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 20, wherein the transfer mechanism comprises:

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a transfer arm having a vacuum line so as to selectively vacuum-absorb the wafers;

a transfer robot for loading and unloading the wafers into the processing chambers [chamber] by moving the transfer arm;

a vertical driving part for moving the transfer robot vertically;

a horizontal driving part for moving the transfer robot horizontally; and

a controller for controlling the transfer robot, the vertical driving part, and the horizontal driving part by applying control signals thereto.

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31. (Amended) A multi-chamber system of an etching facility for manufacturing semiconductor devices comprising:

a first cassette stage for mounting a cassette having unprocessed wafers stacked thereon;

a transfer path adjacent to the first cassette stage that provides space for transportation of wafers, the transfer path being at atmospheric pressure and having a width slightly larger than a diameter of the wafers [having a rectangular shape and providing a space for transportation of wafers];

a plurality of processing chambers arranged in multi-layers and aligned in parallel beside the transfer path;

a transfer mechanism capable of vertical/horizontal reciprocal movement installed in the transfer path for loading and unloading the wafers stacked on the first cassette stage to the plurality of processing chambers; and

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